DESCRIPTION

€9, €3 🐼 🖾

The AZC199-04S a low capacitance of 0.4pF maximum and operates with virtually no insertion loss to 1GHz. This makes the device ideal for protection of high-speed data lines such as USB 2.0, Firewire, DVI. Ethernet and gigabit interfaces. The capacitance low array configuration allows the user to protect four high-speed data or transmission lines. The low voltage inductance construction minimizes overshoot during high current surges. They may be used to meet the ESD immunity requirements of IEC61000-4-2, Level 4 (±15kV air, ±8kV contact discharge).

This device has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and lightning.



FEATURES

- Protects four I/O lines and one Vcc line
- Low capacitance
- Working voltages : 5V
- Low leakage current
- Low capacitance for high-speed interfaces
- No insertion loss to 2.0GHz
- Response Time is < 1 ns

APPLICATIONS

- Digital Visual Interface (DVI)
- USB 1.1/2.0/OTG
- IEEE 1394 Firewire Ports
- Notebooks & Handhelds
- Projection TV & Monitors
- Set-top box
- Flat Panel Displays
- PCI Express

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units	
P _{Pk}	Peak Pulse Power (8/20µs)	150	W	
I _{PP}	Peak Pulse Current (8/20µs)	5	А	
V _{ESD}	ESD per IEC 61000-4-2 (Air)	±15	kV	
200	ESD per IEC 61000-4-2 (Contact)	±8		
T _{OPT}	Operating Temperature	-55/+150	°C	
T _{STG}	Storage Temperature	-55/+150	°C	

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V _{RWM}	Reverse Working Voltage	Any I/O pin to GND			5.0	V
V_{BR}	Reverse Breakdown Voltage	I _⊤ = 1mA Any I/O pin to GND	6.0			V
I _R	Reverse Leakage Current	V _{RWM} = 5V Any I/O pin to GND			1	μA
V _F	Diode Forward Voltage	I _F = 15mA			1.2	V
V _{C1}	Clamping Voltage 1	I _{PP} = 1A, t _p = 8/20µs Any I/O pin to GND			15	V
V _{C2}	Clamping Voltage 2	I _{PP} = 5A, t _p = 8/20µs Any I/O pin to GND			28	V
C _{J1}	Junction Capacitance 1	V _R = 0V, f = 1MHz Between I/O pins			0.4	pF
C _{J2}	Junction Capacitance 2	V _R = 0V, f = 1MHz Any I/O pin to GND			0.8	pF

Note: I/O pins are pin 1,3,4,6.



ELECTRICAL CHARACTERISTICS CURVE

Power Derating Curve

Junction Capacitance vs. Reverse Voltage

UMW® € 3 0 ▲

SOT23-6



1.90

0.45

0.59REF 0.25BSC

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1.80

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0.10

0.10

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3. 6'

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L1 L2

R1

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◬ θ 2.00

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0.20

8° 7°

14'



Marking

8	B	_8_	
C16QL			
- Fla	H	H	

Ordering information

Order code	Package	Base qty	Delivery mode
UMW AZC199-04S	SOT23-6	3000	Tape and reel

单击下面可查看定价,库存,交付和生命周期等信息

>>UMW(友台半导体)